

Silicon Diffused Power Transistor**BUT11AF****GENERAL DESCRIPTION**

High-voltage, high-speed glass-passivated npn power transistor in a SOT186 envelope with electrically insulated mounting base, intended for use in converters, inverters, switching regulators, motor control systems, etc.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1000	V
V_{CEO}	Collector-emitter voltage (open base)		-	450	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	10	A
P_{tot}	Total power dissipation		-	20	W
V_{CESat}	Collector-emitter saturation voltage		-	1.5	V
I_{CSat}	Collector saturation current		2.5	-	A
t_f	Fall time		800	-	ns

[INCLUDE]**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1000	V
V_{CEO}	Collector-emitter voltage (open base)		-	450	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	10	A
I_B	Base current (DC)		-	2	A
I_{BM}	Base current peak value		-	4	A
P_{tot}	Total power dissipation		-	20	W
T_{stg}	Storage temperature		-65	150	$^{\circ}\text{C}$
T_j	Junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Junction to heatsink	with heatsink compound	-	3.95	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	55	-	K/W

ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. $\leq 65\%$; clean and dustfree	-		1500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	12	-	pF

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STATIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES}	Collector cut-off current ¹	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	-	-	1.0	mA
I _{CES}		V _{BE} = 0 V; V _{CE} = V _{CESMmax} T _j = 125 °C	-	-	2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 9 V; I _C = 0 A	-	-	10	mA
V _{CEOsust}	Collector-emitter sustaining voltage	I _B = 0 A; I _C = 100 mA; L = 25 mH	450	-	-	V
V _{CEsat}	Collector-emitter saturation voltages	I _C = 2.5 A; I _B = 0.5 A	-	-	1.5	V
V _{BEsat}		I _C = 2.5 A; I _B = 0.5 A	-	-	1.3	V
h _{FE}	DC current gain	I _C = 5 mA; V _{CE} = 5 V	10	18	35	
h _{FE}		I _C = 500 mA; V _{CE} = 5 V	10	20	35	

DYNAMIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
t _{on}	Switching times (resistive load)	I _{Con} = 2.5 A; I _{Bon} = -I _{Boff} = 0.5 A	-	1	μs
t _s	Turn-on time		-	4	μs
t _f	Turn-off storage time		-	0.8	μs
t _s	Switching times (inductive load)	I _{Con} = 2.5 A; I _{Bon} = 0.5 A; L _B = 1 μH; -V _{BB} = 5 V	1.1	1.4	μs
t _f	Turn-off storage time		80	150	ns
t _s	Switching times (inductive load)	I _{Con} = 2.5 A; I _{Bon} = 0.5 A; L _B = 1 μH; -V _{BB} = 5 V; T _j = 100 °C	1.2	1.5	μs
t _f	Turn-off storage time		140	300	ns

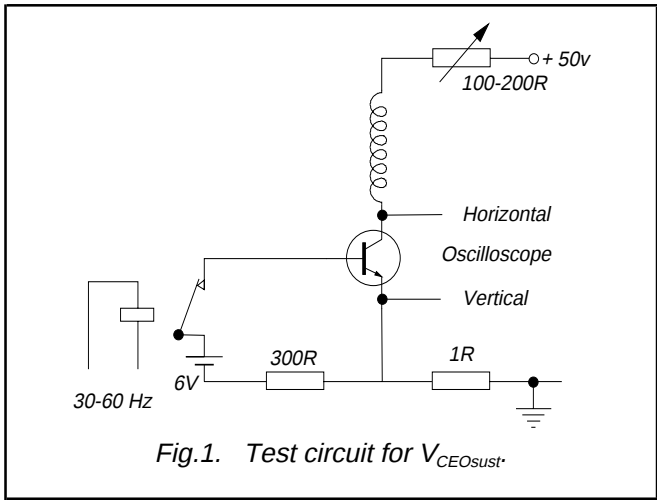


Fig.1. Test circuit for V_{CEOsust}

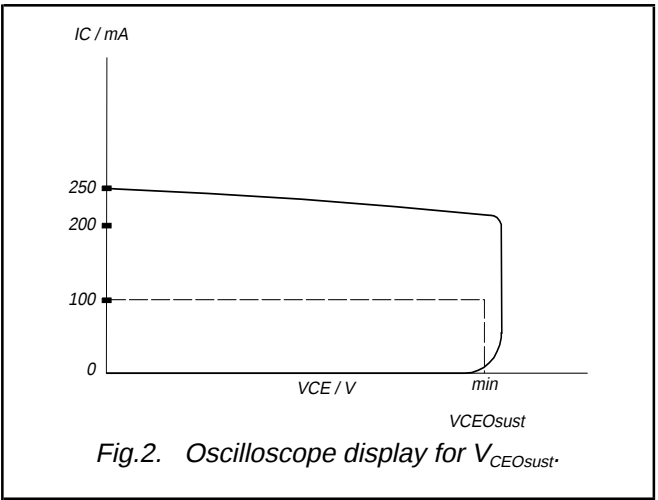
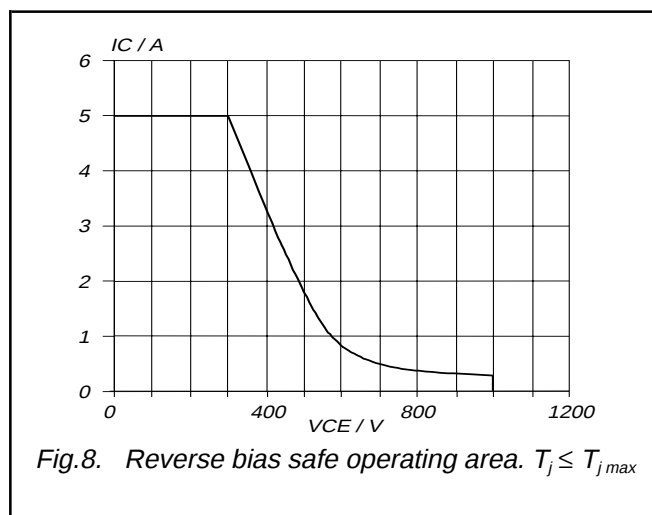
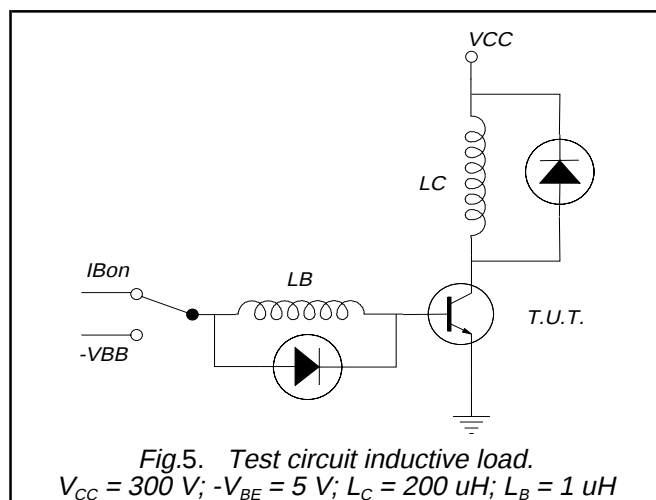
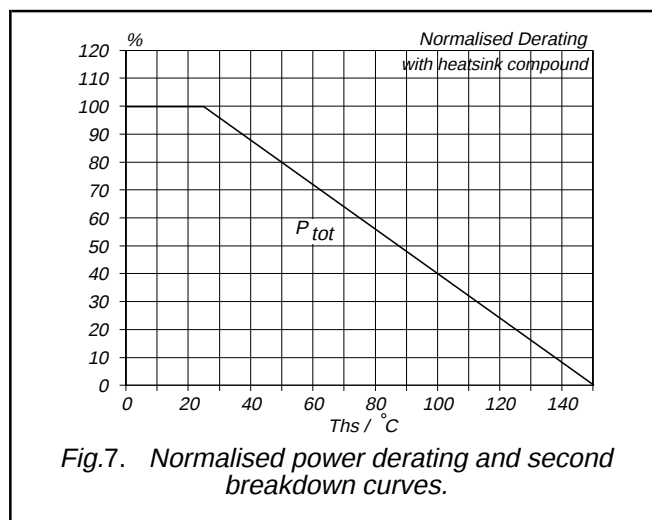
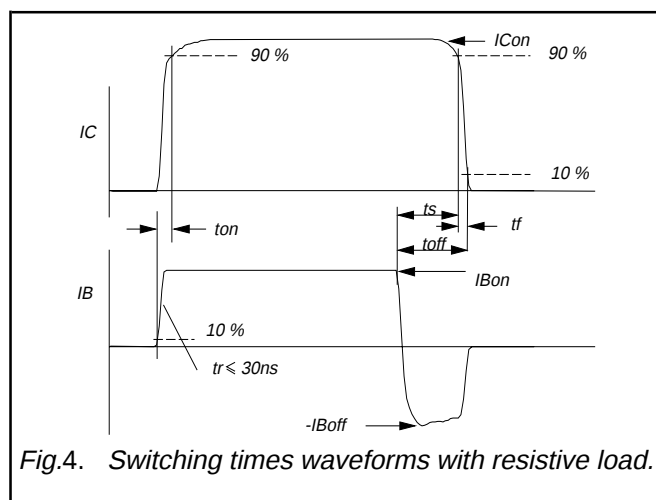
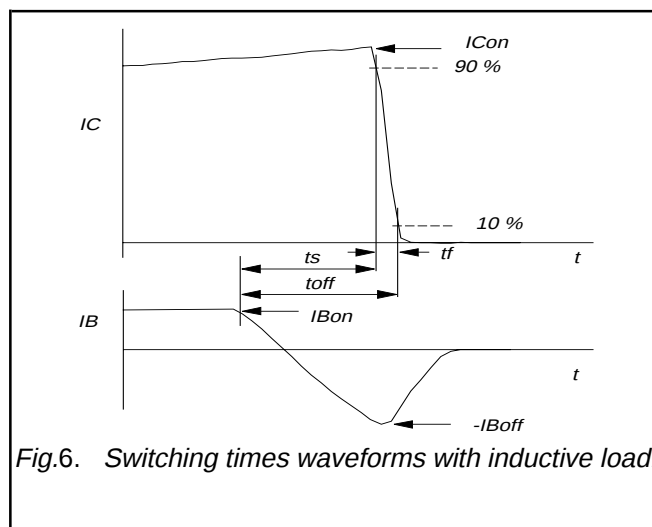
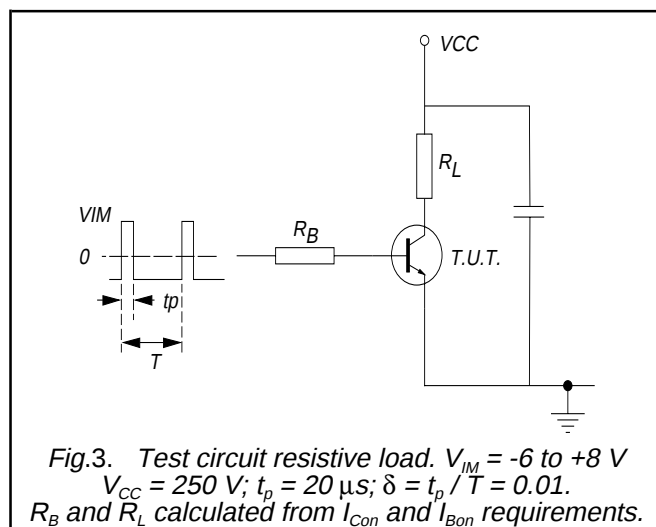


Fig.2. Oscilloscope display for V_{CEOsust}

¹ Measured with half sine-wave voltage (curve tracer).

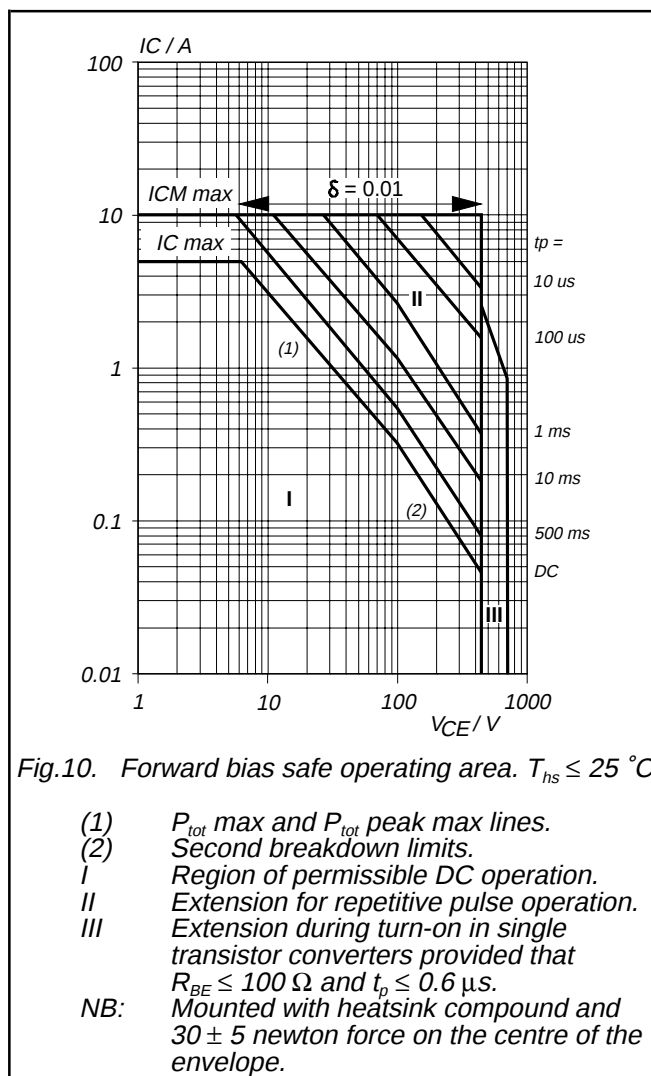
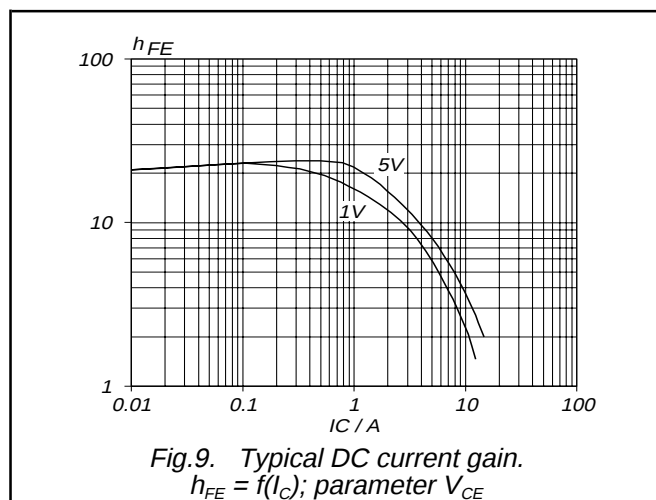
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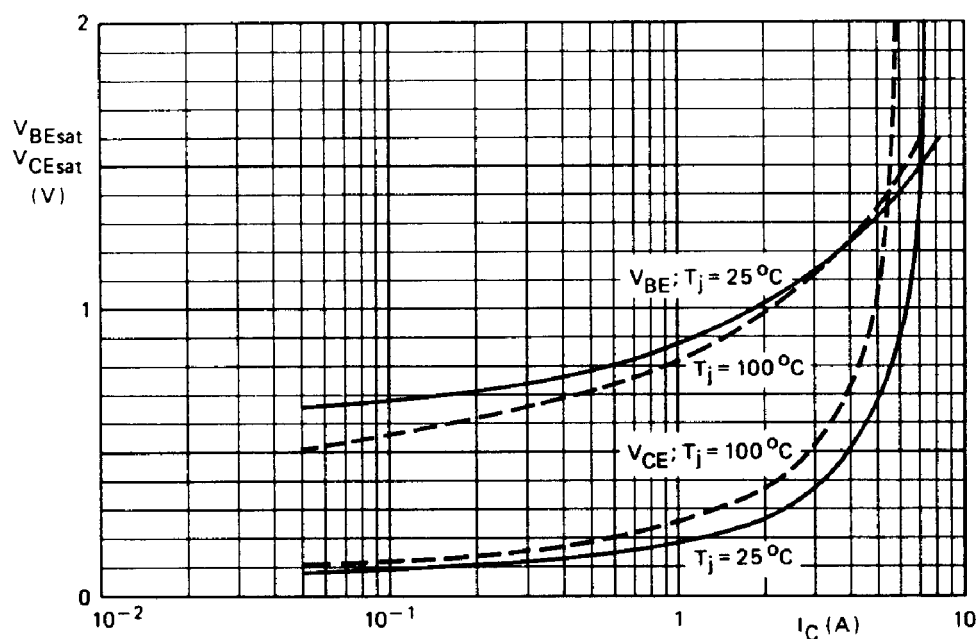


Fig.11. Typical base-emitter and collector-emitter saturation voltages.

$$V_{BEsat} = f(I_C); V_{CEsat} = f(I_C); I_C/I_B = 5$$

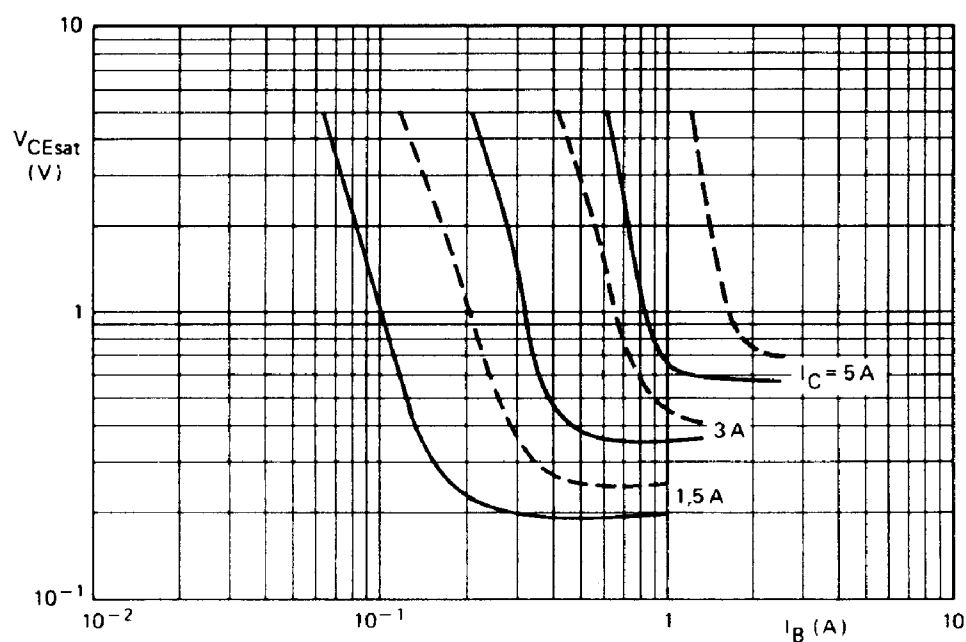


Fig.12. Collector-emitter saturation voltage. Solid lines = typ values, dotted lines = max values. $V_{CEsat} = f(I_B)$; parameter I_C

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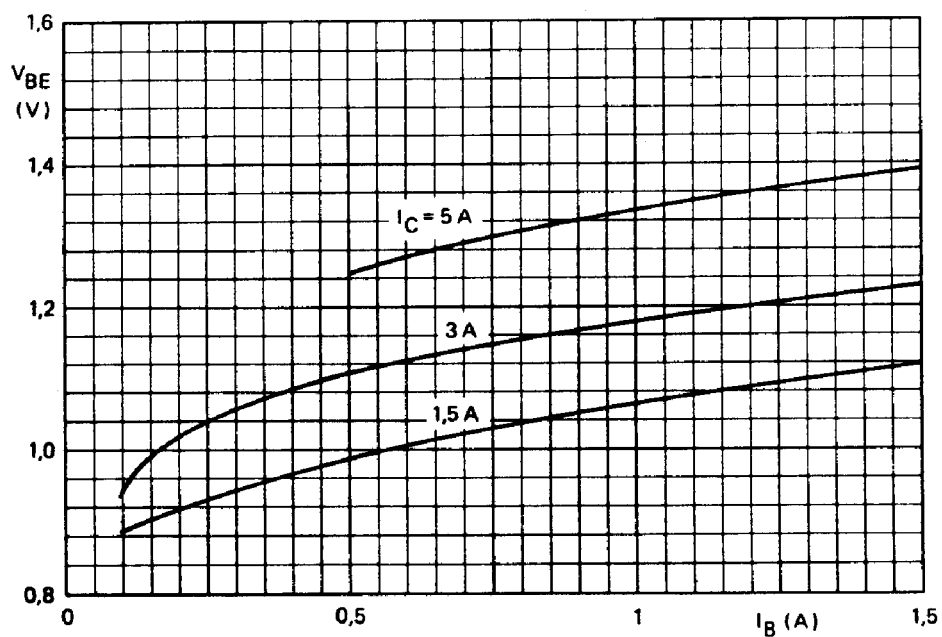


Fig.13. Typical base-emitter saturation voltage.
 $V_{BEsat} = f(I_B)$; parameter I_C

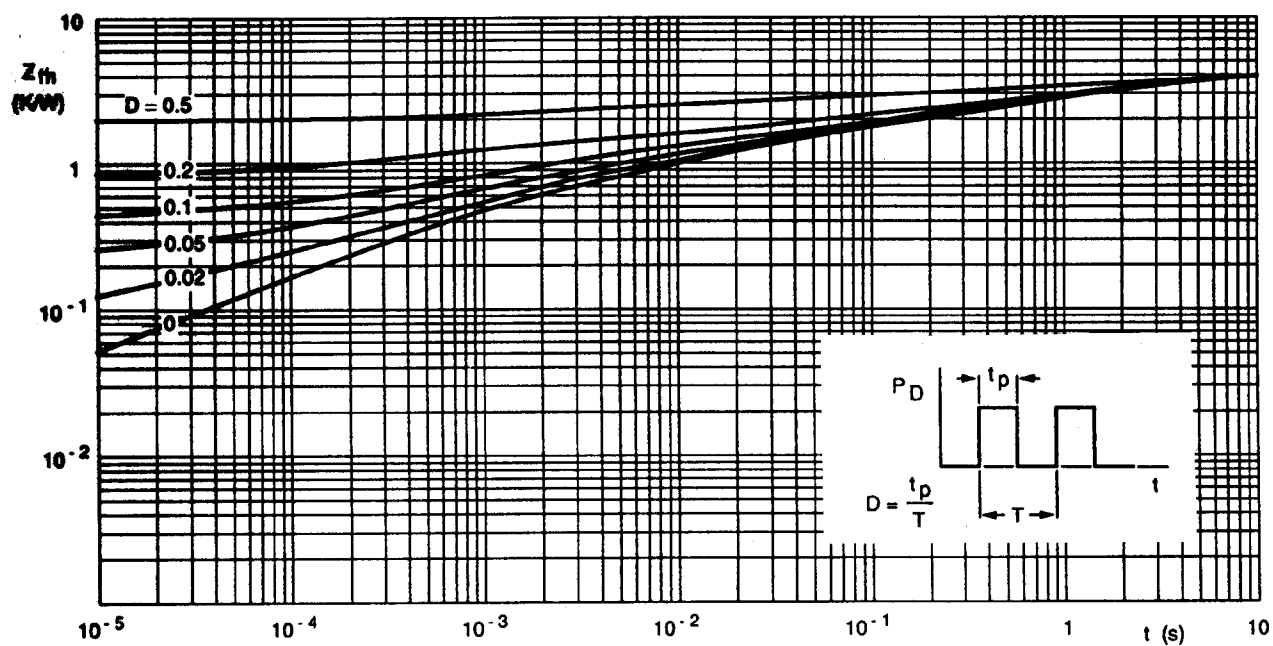


Fig.14. Transient thermal impedance.
 $Z_{thj-hs} = f(t)$; parameter $D = t_p/T$

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

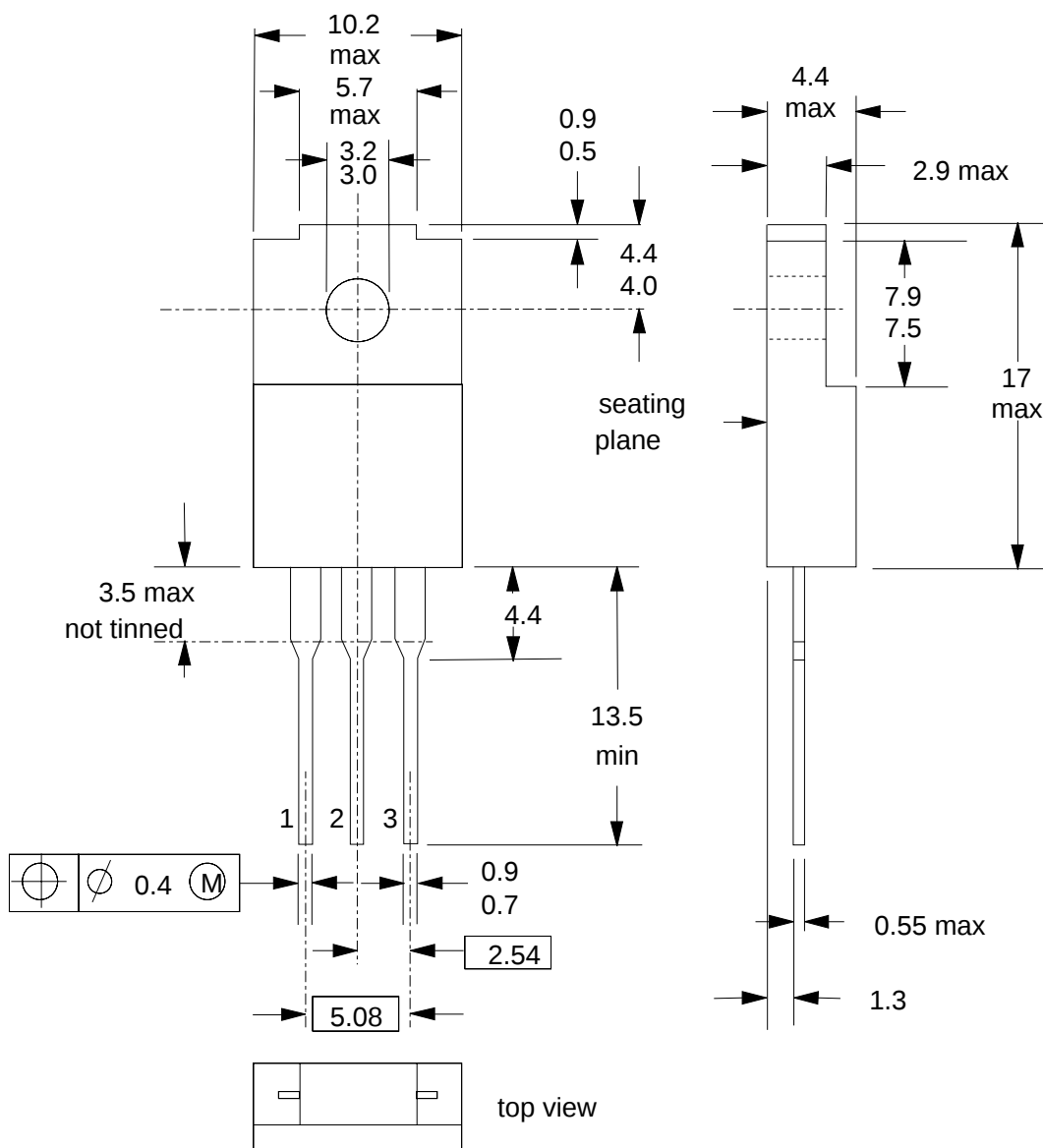


Fig.15. SOT186; The seating plane is electrically isolated from all terminals.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for F-pack envelopes.
3. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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